



MMIC SURFACE MOUNT

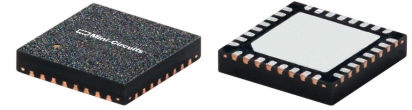
# Power Amplifier

## PMA5-63-2W+

50Ω 10 to 6000 MHz 2 W P<sub>SAT</sub>

### THE BIG DEAL

- P1dB, Typ. +31.2 dBm
- P<sub>SAT</sub>, Typ. +33.8 dBm
- Low Noise Figure, Typ. 2.7 dB
- High OIP3, Typ. +44.5 dBm
- Supply Voltage +12 V, 400 mA
- 5x5 mm 32-Lead QFN-Style Package

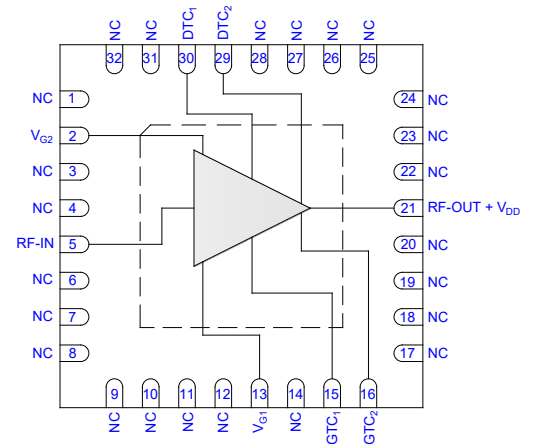


Generic photo used for illustration purposes only

### APPLICATIONS

- Test and Measurement Equipment
- Radar, EW, and ECM Defense Systems
- 5G Sub6, MIMO Wireless Infrastructure Systems
- Microwave Radio & VSAT

### FUNCTIONAL DIAGRAM



### PRODUCT OVERVIEW

The PMA5-63-2W+ is a GaAs MMIC Distributed Power Amplifier operating from 10 to 6000 MHz. The amplifier provides 12 dB of gain, +33.8 dBm saturated output power, and achieves +44.5 dBm output IP3, while operating from a +12 V power supply and consuming 400 mA of quiescent current. In addition, it is internally matched to 50 Ohms and comes in a 5x5 mm 32-Lead QFN-Style package. These characteristics make it ideally suited for wideband test instrumentation and defense systems that require high operating output power, while maintaining very low distortion characteristics.

### KEY FEATURES

Features	Advantages
High P1dB (Typ. +31.2 dBm) and P <sub>SAT</sub> (Typ. +33.8 dBm)	Flat, broadband gain and high output power without high frequency roll-off make this device excellent for wideband systems from 10 to 6000 MHz that require at least 1 W of linear operating output power over the full band.
Low Noise Figure Typ. 2.7 dB	High operating output power accompanied with low noise figure enables a significant signal to noise ratio advantage for systems requiring high dynamic range.
High OIP3 Typ. +44.5 dBm	High operating OIP3 and low 2nd and 3rd harmonic response provides for very low in-band distortion products, enabling minimal signal degradation in high fidelity measurement systems and demanding communication systems.
5x5 mm 32-Lead QFN-Style Package	Small footprint saves space in dense layouts while providing low inductance, repeatable transitions, and excellent thermal contact to the PCB. Industry standard packaging allows for ease of assembly in high volume manufacturing processes.





MMIC SURFACE MOUNT

# Power Amplifier

**PMA5-63-2W+**

Mini-Circuits

50Ω 10 to 6000 MHz 2 W P<sub>SAT</sub>**ELECTRICAL SPECIFICATIONS<sup>1</sup> AT +25°C, V<sub>DD</sub> = +12 V, UNLESS NOTED OTHERWISE**

Parameter	Condition (MHz)	Min.	Typ.	Max.	Units
Frequency Range		10		6000	MHz
Gain	10		17.9		dB
	2000	11.0	12.2		
	4000	10.8	12.0		
	6000	10.0	11.9		
Output Power at 1 dB Compression (P <sub>1dB</sub> )	10		+28.2		dBm
	2000		+30.6		
	4000		+31.2		
	6000		+30.9		
Output Power at Saturation (P <sub>SAT</sub> ) <sup>2</sup>	10		+32.9		dBm
	2000		+33.0		
	4000		+33.8		
	6000		+33.6		
Output Third-Order Intercept (P <sub>OUT</sub> = +20 dBm/Tone)	10		+42.5		dBm
	2000		+45.0		
	4000		+44.5		
	6000		+42.3		
Output Second-Order Intercept (P <sub>OUT</sub> = +20 dBm/Tone)	10		+63.1		dBm
	2000		+44.5		
	4000		+42.3		
	6000		+42.1		
2nd Harmonic <sup>3</sup> (P <sub>OUT</sub> = +10 dBm/Tone)	10		-61.0		dBc
	2000		-42.6		
	4000		-40.6		
	6000		-40.0		
Input Return Loss	10		23		dB
	2000		12		
	4000		28		
	6000		25		
Output Return Loss	10		24		dB
	2000		12		
	4000		10		
	6000		13		
Isolation	10		50		dB
	2000		46		
	4000		41		
	6000		37		
Noise Figure	500		6.8		dB
	2000		3.8		
	4000		2.7		
	6000		2.7		
Device Operating Voltage (V <sub>DD</sub> )			+12	+16	V
Device Operating Current (I <sub>DD</sub> ) <sup>4</sup>			400		mA
Gate Voltage (V <sub>G1</sub> ) <sup>5</sup>		-2.0	-0.8	-0.2	V
Gate Current (I <sub>G1</sub> )			15	4,000	μA
Gate Voltage (V <sub>G2</sub> )		+2	+5	+7.5	V
Gate Current (I <sub>G2</sub> )			15	4,000	μA
DC Current Variation vs. Temperature <sup>6</sup>			11		μA/°C

1. Tested on Mini-Circuits Characterization Test Board. See Figure 2. Board loss de-embedded.

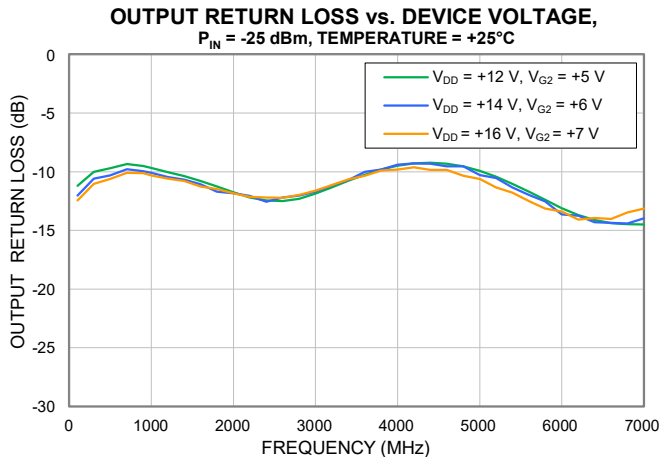
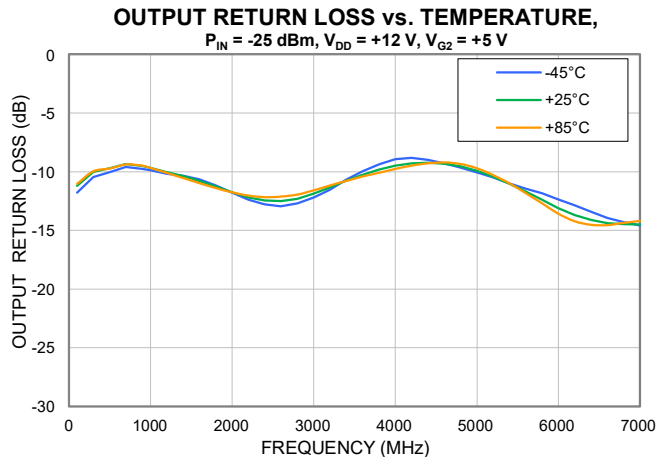
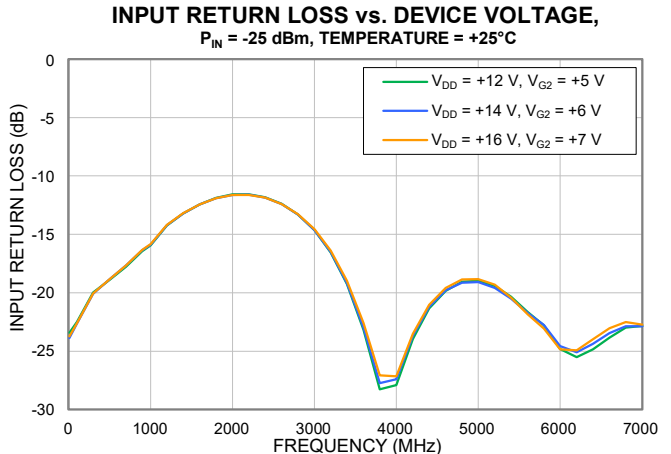
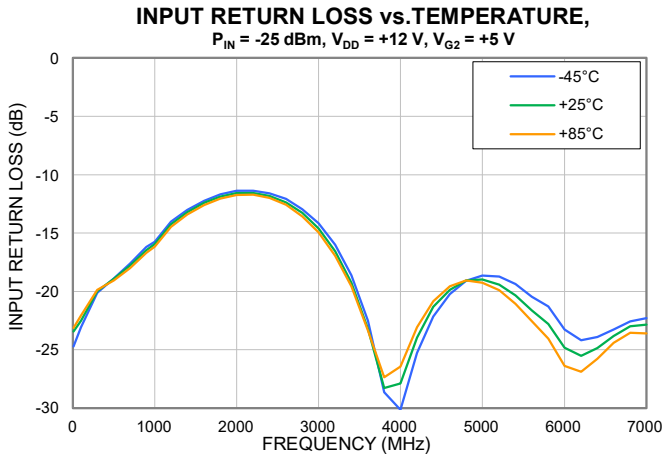
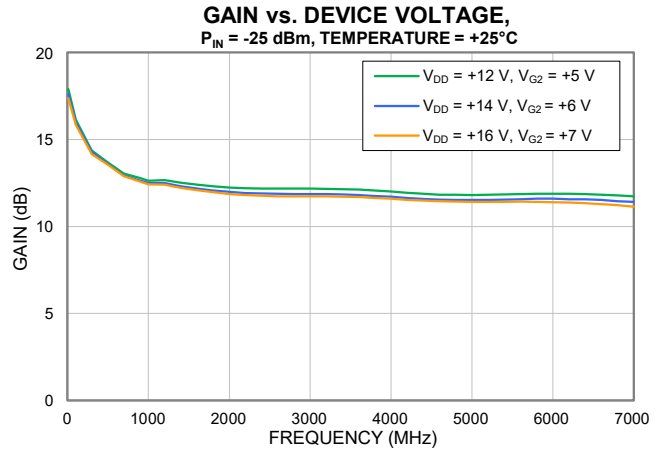
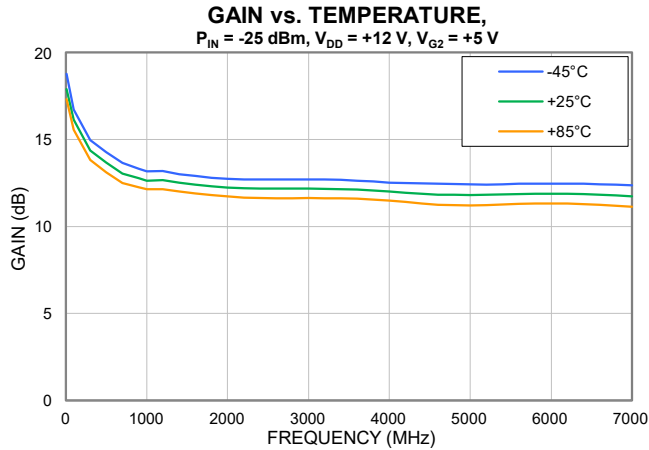
2. P<sub>SAT</sub> defined as when the Output Power changes 0.1 dB per 1 dB change in Input Power.

3. 2nd harmonic measured at 2x the input frequency shown.

4. Current at P<sub>IN</sub> = -25 dBm. Increases to 650 mA at P<sub>1dB</sub>.5. Adjust V<sub>G1</sub> between -2.0 V and -0.5 V to achieve I<sub>DD</sub> = 400 mA.6. (Current at +85°C - Current at -45°C)/(+130°C). V<sub>G1</sub> held constant over temperature.



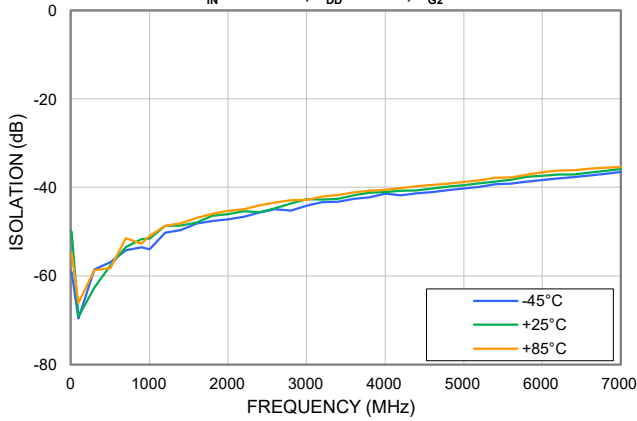
### TYPICAL PERFORMANCE GRAPHS



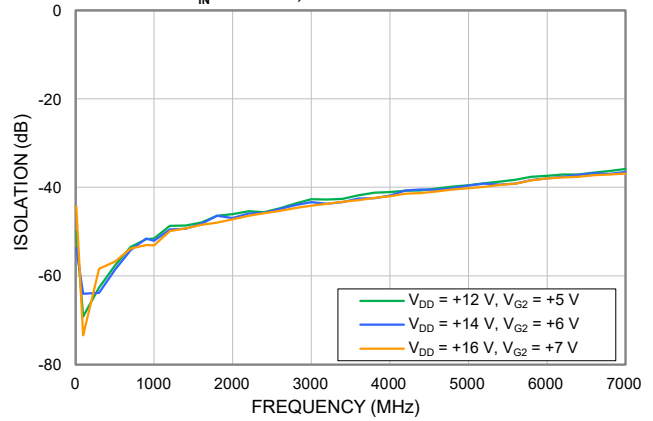


### TYPICAL PERFORMANCE GRAPHS

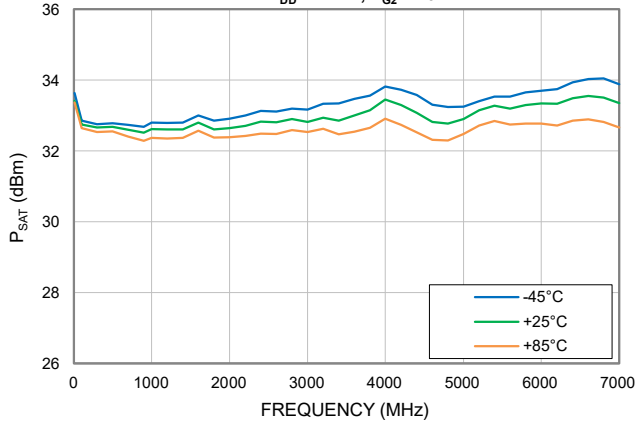
**ISOLATION vs. TEMPERATURE,**  
P<sub>IN</sub> = -25 dBm, V<sub>DD</sub> = +12 V, V<sub>G2</sub> = +5 V



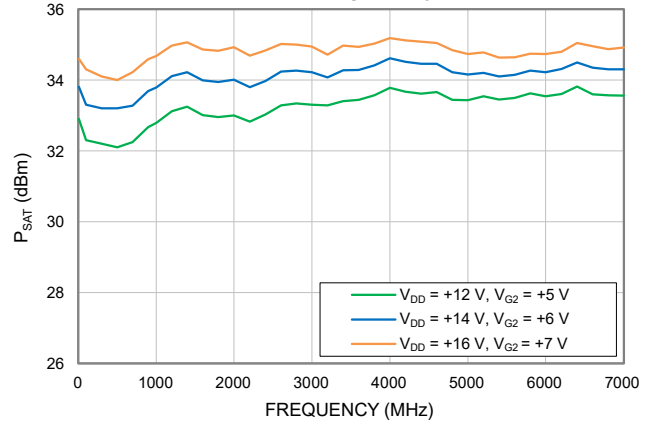
**ISOLATION vs. DEVICE VOLTAGE,**  
P<sub>IN</sub> = -25 dBm, TEMPERATURE = +25°C



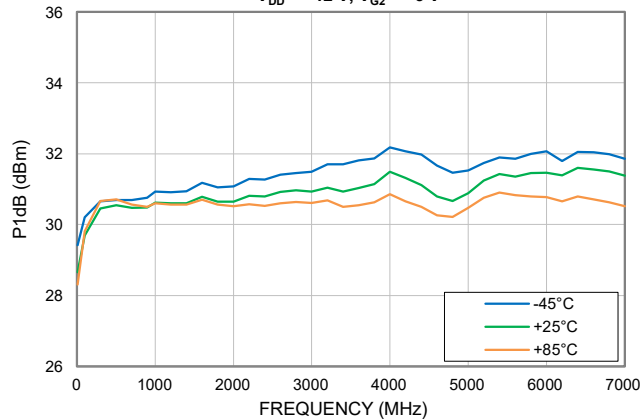
**P<sub>SAT</sub> vs. TEMPERATURE,**  
V<sub>DD</sub> = +12 V, V<sub>G2</sub> = +5 V



**P<sub>SAT</sub> vs. DEVICE VOLTAGE,**  
TEMPERATURE = +25°C



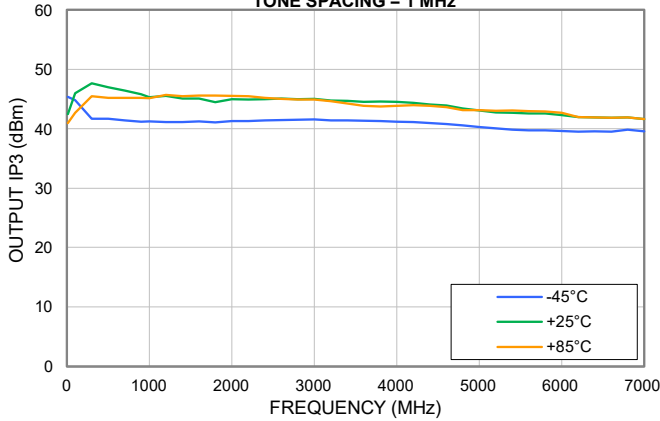
**P1dB vs. TEMPERATURE,**  
V<sub>DD</sub> = +12 V, V<sub>G2</sub> = +5 V



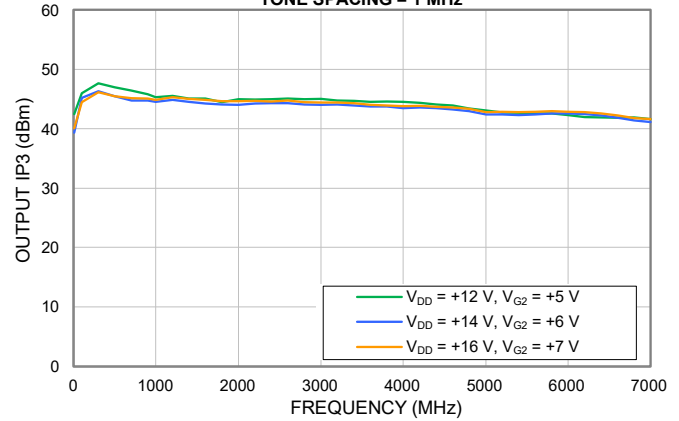


### TYPICAL PERFORMANCE GRAPHS

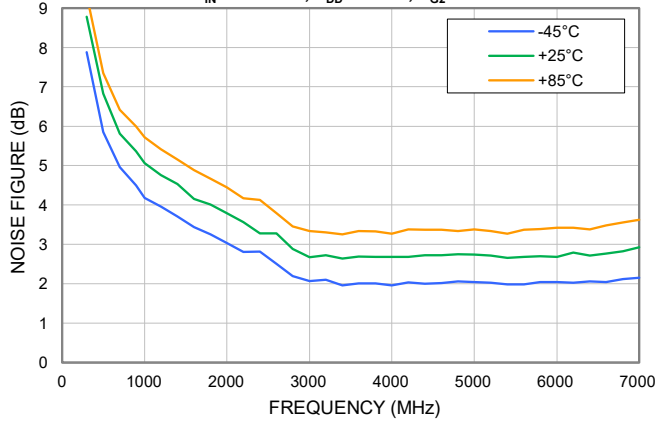
**OUTPUT IP3 vs. TEMPERATURE,**  
P<sub>OUT</sub> = +20 dBm/TONE, V<sub>DD</sub> = +12 V, V<sub>G2</sub> = +5 V  
TONE SPACING = 1 MHz



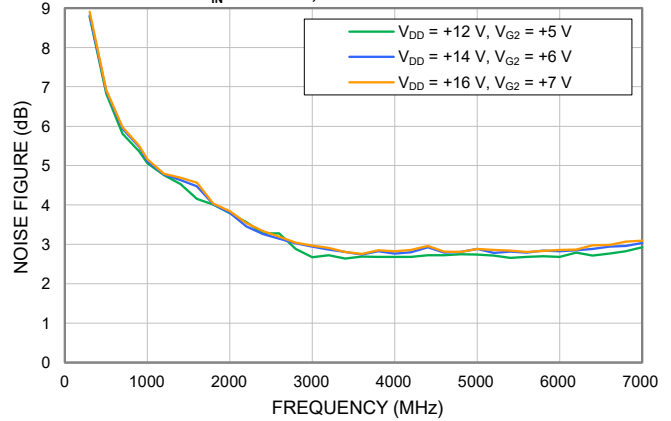
**OUTPUT IP3 vs. DEVICE VOLTAGE,**  
P<sub>OUT</sub> = +20 dBm/TONE, TEMPERATURE = +25°C  
TONE SPACING = 1 MHz



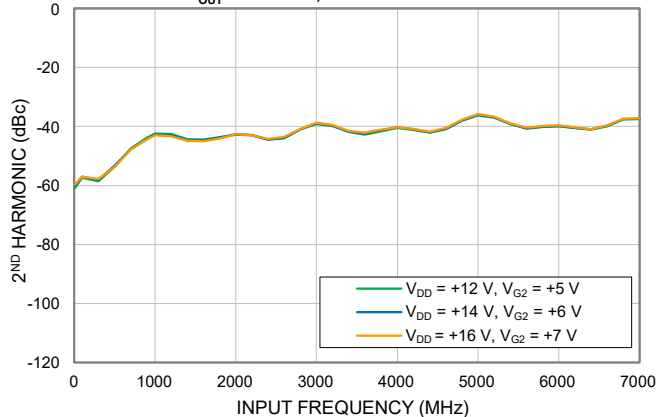
**NOISE FIGURE vs. TEMPERATURE,**  
P<sub>IN</sub> = -25 dBm, V<sub>DD</sub> = +12 V, V<sub>G2</sub> = +5 V



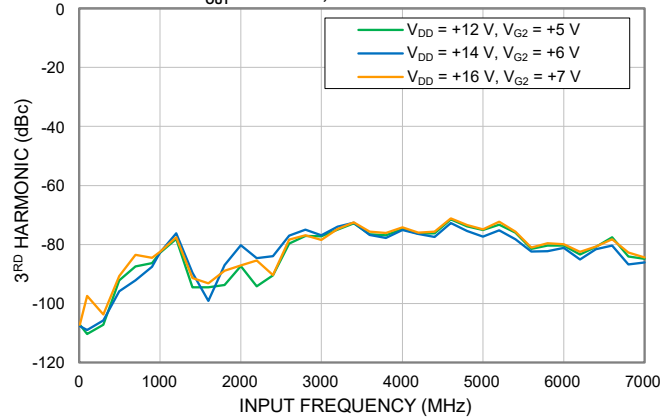
**NOISE FIGURE vs. DEVICE VOLTAGE,**  
P<sub>IN</sub> = -25 dBm, TEMPERATURE = +25°C



**2<sup>ND</sup> HARMONIC vs. DEVICE VOLTAGE,**  
P<sub>OUT</sub> = +10 dBm, TEMPERATURE = +25°C



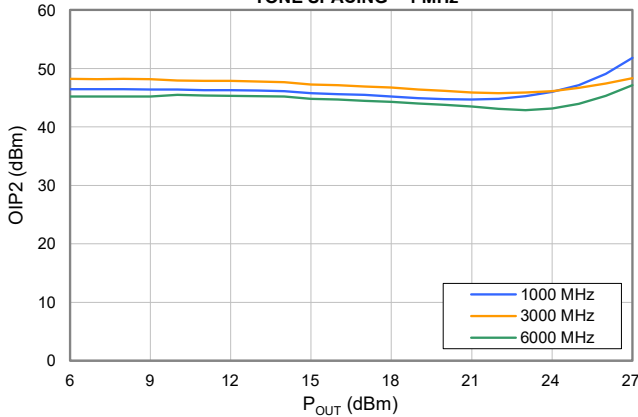
**3<sup>RD</sup> HARMONIC vs. DEVICE VOLTAGE,**  
P<sub>OUT</sub> = +10 dBm, TEMPERATURE = +25°C



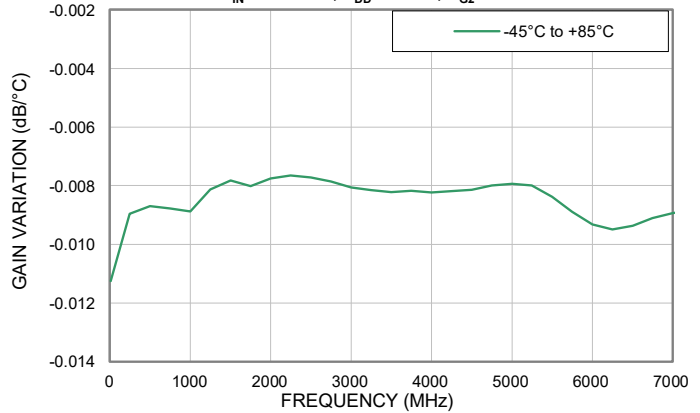


### TYPICAL PERFORMANCE GRAPHS

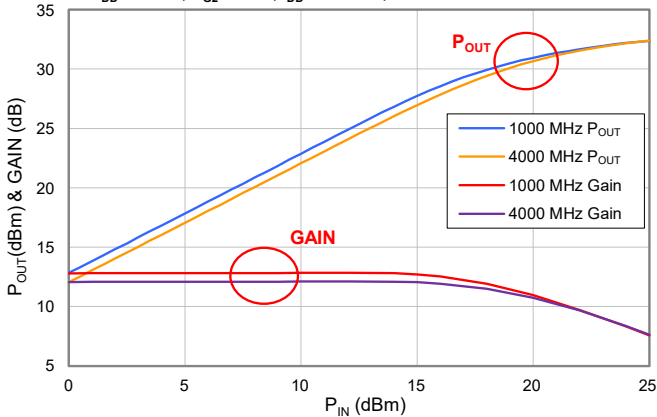
**OUTPUT IP2 vs. P<sub>OUT</sub>/TONE**  
V<sub>DD</sub> = +12 V, V<sub>G2</sub> = +5 V, TEMPERATURE = +25°C,  
TONE SPACING = 1 MHz



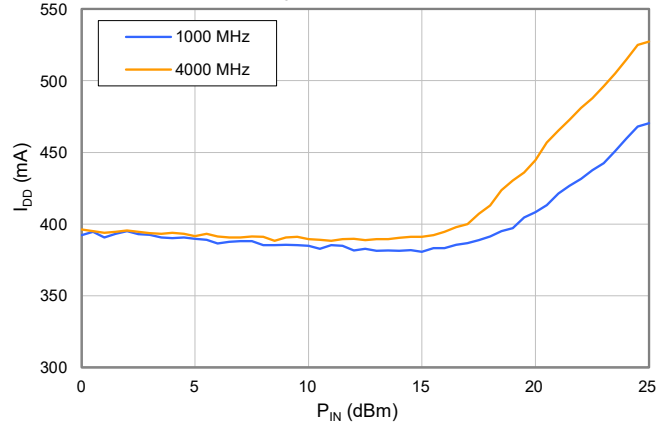
**GAIN VARIATION vs. TEMPERATURE,**  
P<sub>IN</sub> = -25 dBm, V<sub>DD</sub> = +12 V, V<sub>G2</sub> = +5 V



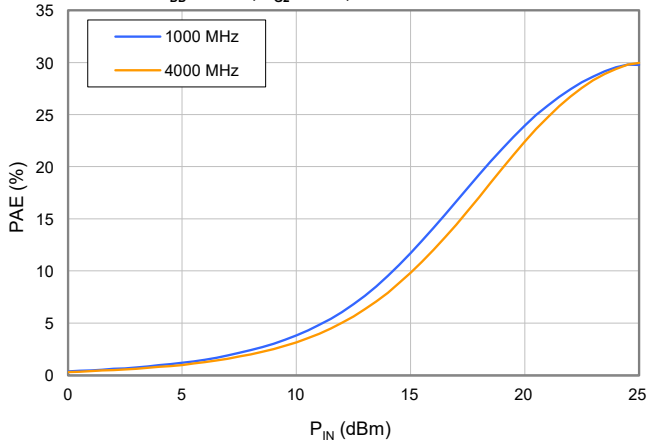
**P<sub>OUT</sub> & GAIN vs. P<sub>IN</sub>**  
V<sub>DD</sub> = +12 V, V<sub>G2</sub> = +5 V, I<sub>DD</sub> = 400 mA, TEMPERATURE = +25°C



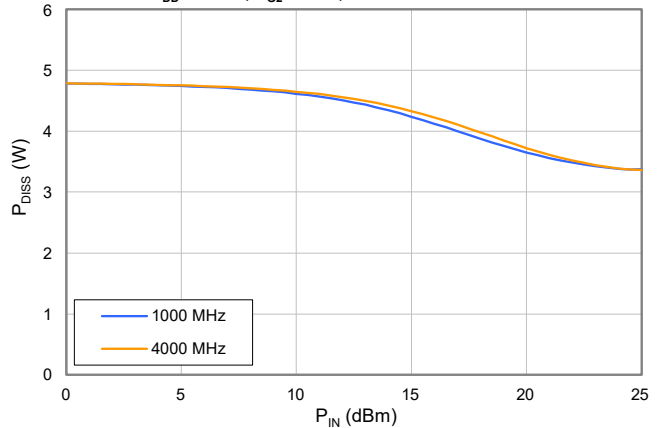
**I<sub>DD</sub> vs. P<sub>IN</sub>**  
V<sub>DD</sub> = +12 V, V<sub>G2</sub> = +5 V, TEMPERATURE = +25°C



**PAE vs. P<sub>IN</sub>**  
V<sub>DD</sub> = +12 V, V<sub>G2</sub> = +5 V, TEMPERATURE = +25°C

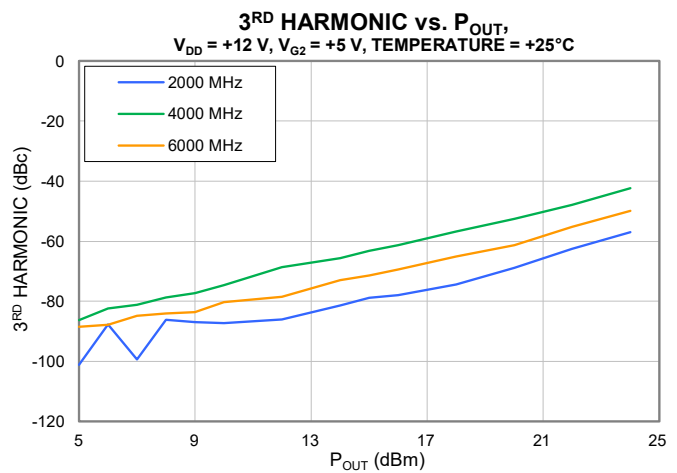
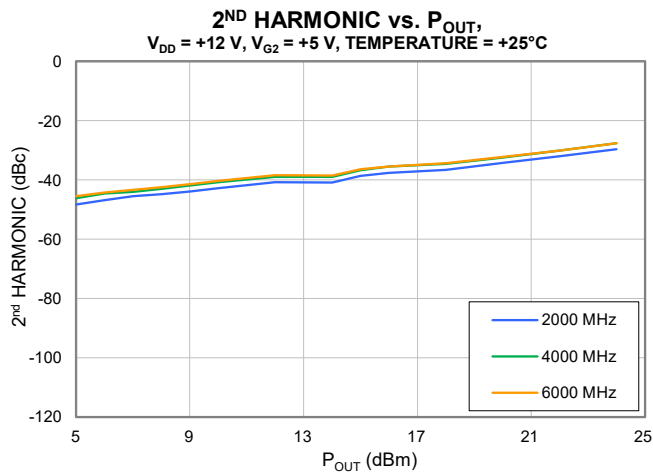
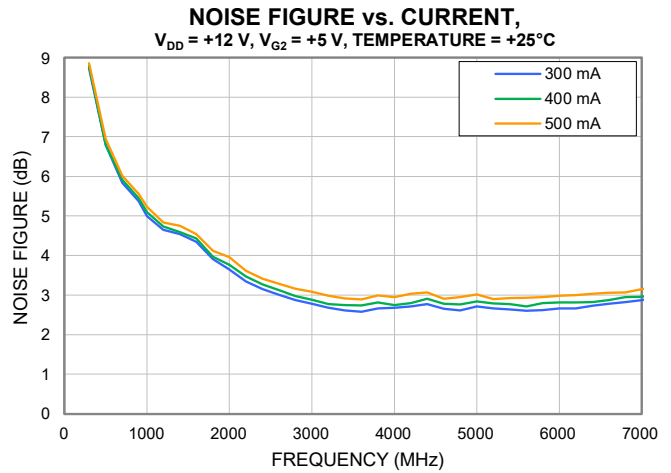
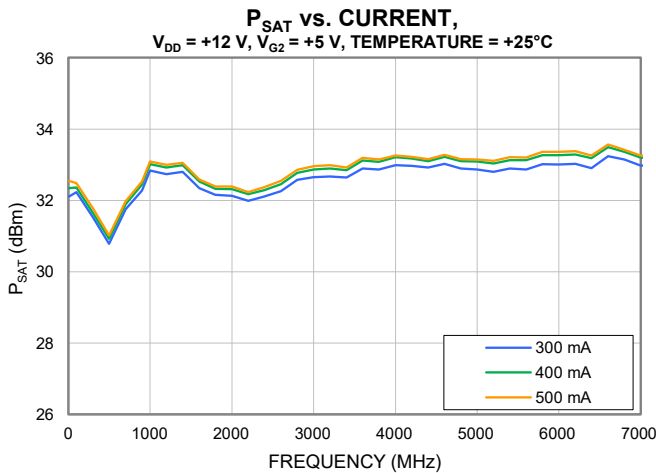
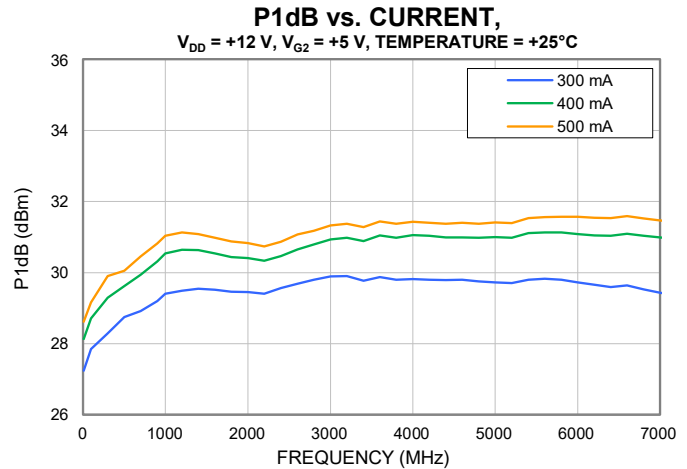
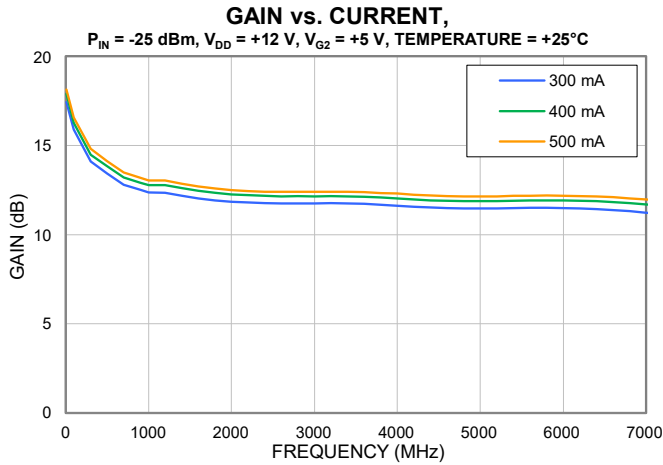


**P<sub>DISS</sub> vs. P<sub>IN</sub>**  
V<sub>DD</sub> = +12 V, V<sub>G2</sub> = +5 V, TEMPERATURE = +25°C





### TYPICAL PERFORMANCE GRAPHS





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# Power Amplifier

## PMA5-63-2W+

50Ω 10 to 6000 MHz 2 W P<sub>SAT</sub>

### ABSOLUTE MAXIMUM RATINGS<sup>7</sup>

Parameter	Ratings
Operating Temperature (ground lead)	-45°C to +85°C
Storage Temperature	-65°C to +150°C
Junction Temperature <sup>8</sup>	+175°C
Total Power Dissipation	10 W
Input Power (CW), V <sub>DD</sub> = +12 V	+31 dBm
DC Voltage at RF-OUT + V <sub>DD</sub>	+16.5 V
DC Gate Voltage at V <sub>G1</sub>	-0.2 V
DC Gate Voltage at V <sub>G2</sub>	+7.5 V
DC Gate Current at V <sub>G1</sub> (I <sub>G1</sub> )	4.5 mA
DC Gate Current at V <sub>G2</sub> (I <sub>G2</sub> )	4.5 mA

7. Permanent damage may occur if any of these limits are exceeded. Maximum ratings are not intended for continuous normal operation.

8. Peak temperature on top of Die.

### THERMAL RESISTANCE

Parameter	Ratings
Thermal Resistance (Θ <sub>JC</sub> ) <sup>9</sup>	6°C/W

9. Θ<sub>JC</sub> = (Hot Spot Temperature on Die - Temperature at Ground Lead)/Dissipated Power

### ESD RATING

	Class	Voltage Range	Reference Standard
HBM	1A	250 V to < 500 V	ANSI/ESDA/JEDEC JS-001-2023
CDM	C2	500 V to < 1,000 V	ANSI/ESDA/JEDEC JS-002-2022



ESD HANDLING PRECAUTION: This device is designed to be Class 1A for HBM. Static charges may easily produce potentials higher than this with improper handling and can discharge into DUT and damage it. As a preventive measure Industry standard ESD handling precautions should be used at all times to protect the device from ESD damage.

### MSL RATING

Moisture Sensitivity: MSL1 in accordance with IPC/JEDEC J-STD-020E/JEDEC J-STD-033C







### FUNCTIONAL DIAGRAM

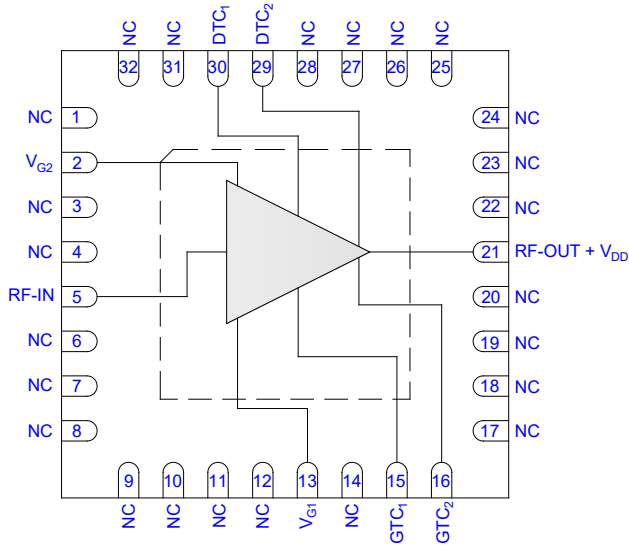


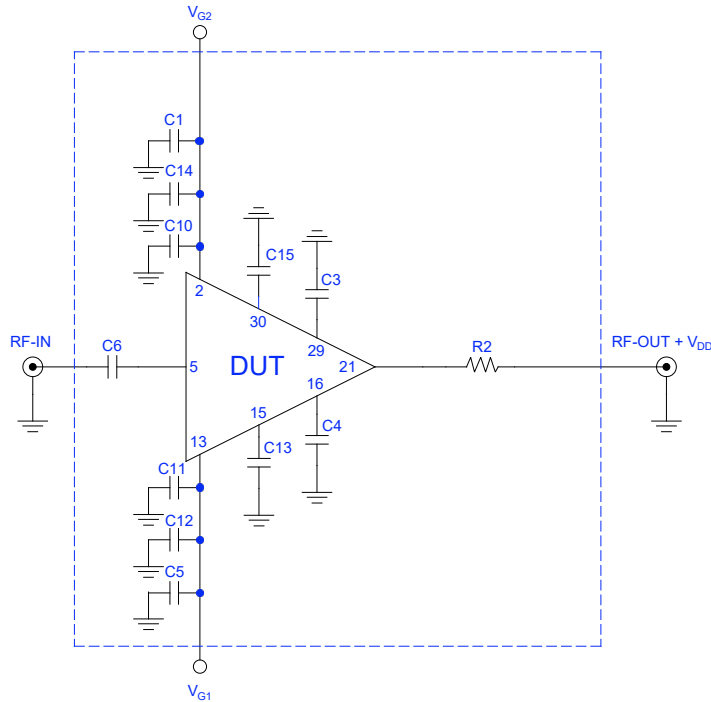
Figure 1. PMA5-63-2W+ Functional Diagram

### PAD DESCRIPTION

Function	Pad Number	Description (Refer to Figure 1)
RF-IN	5	RF-IN Pad connects to RF Input port.
RF-OUT + V <sub>DD</sub>	21	RF-OUT Pad connects to RF Output port. V <sub>DD</sub> is applied via external bias tee.
V <sub>G1</sub>	13	Gate 1 control voltage.
V <sub>G2</sub>	2	Gate 2 control voltage.
DTC <sub>1</sub>	30	Drain Low Frequency Termination Capacitor (AC GND)
DTC <sub>2</sub>	29	Drain Low Frequency Termination Capacitor (AC GND)
GTC <sub>1</sub>	15	Gate Low Frequency Termination Capacitor (AC GND)
GTC <sub>2</sub>	16	Gate Low Frequency Termination Capacitor (AC GND)
NC	1, 3, 4, 6-12, 14, 17-20, 22-28, 31, 32	Not used internally. Connected to ground on test board.
GND	Paddle	Connects to ground.



### CHARACTERIZATION TEST BOARD



#### Electrical Parameters and Conditions

Gain, Return Loss, Output Power at 1 dB Compression (P1dB), Output IP3 (OIP3), and Noise Figure measured using N5242B PNA-X Microwave Network Analyzer. Device bias voltage V<sub>DD</sub> supplied by external Bias-Tee.

#### Conditions:

1. Gain and Return Loss: P<sub>IN</sub> = -25 dBm
2. Output IP3 (OIP3): Two tones, spaced 1MHz apart, +20 dBm/Tone at output.

#### Power ON/ Power OFF Sequence

Caution: Permanent damage to the device will occur if the Power ON/ Power OFF sequences are not followed.

#### Power ON:

1. Set V<sub>G1</sub> = -2 V and Turn ON.
2. Set V<sub>G2</sub> = +5 V and Turn ON.
3. Set V<sub>DD</sub> = +12 V and Turn ON.
4. Increase V<sub>G1</sub> to desired I<sub>DD</sub>.
5. Turn ON RF signal.

#### Power OFF:

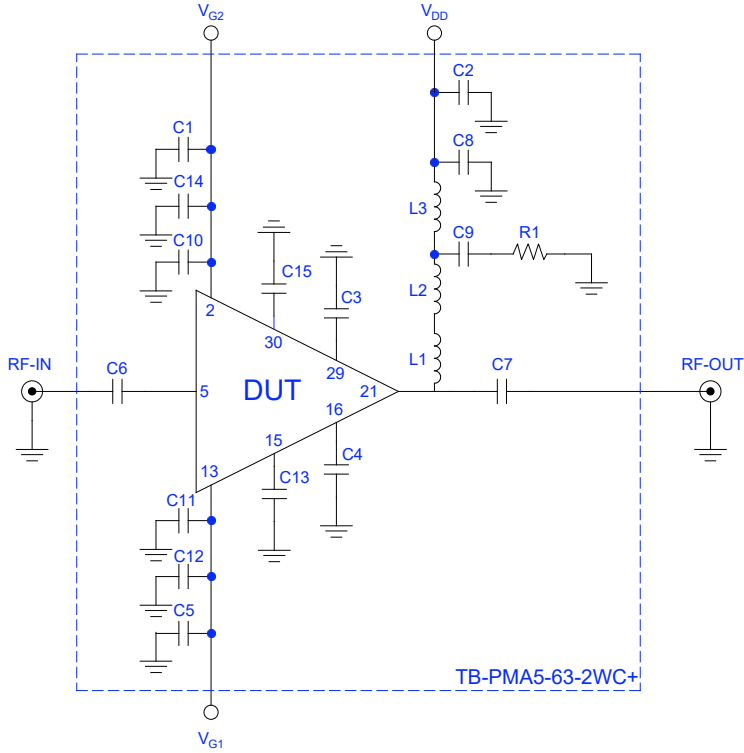
1. Turn OFF RF signal.
2. Decrease V<sub>G1</sub> to -2 V.
3. Turn OFF V<sub>DD</sub>.
4. Turn OFF V<sub>G2</sub>.
5. Turn OFF V<sub>G1</sub>.

Figure 2. PMA5-63-2W+ Characterization Test Board

Component	Value	Size	Part Number	Manufacturer
R2	0Ω	0402	RK73Z1ETTP	KOA SPEER ELECTRONICS
C1, C3, C4, C5	4.7 μF	1206	12063C475KAT2A	AVX CORPORATION
C6	0.1 μF	0402	GRM155R71E104KE14D	MURATA
C10, C11	100 pF	0402	GRM1555C1H101JA01D	MURATA
C12, C13, C14, C15	1 nF	0402	GRM1555C1H102JA01D	MURATA



### EVALUATION BOARD



#### Power ON/ Power OFF Sequence

Caution: Permanent damage to the device will occur if the Power ON/ Power OFF sequences are not followed.

#### Power ON:

1. Set  $V_{G1} = -2\text{ V}$  and Turn ON.
2. Set  $V_{G2} = +5\text{ V}$  and Turn ON.
3. Set  $V_{DD} = +12\text{ V}$  and Turn ON.
4. Increase  $V_{G1}$  to desired  $I_{DD}$ .
5. Turn ON RF signal.

#### Power OFF:

1. Turn OFF RF signal.
2. Decrease  $V_{G1}$  to  $-2\text{ V}$ .
3. Turn OFF  $V_{DD}$ .
4. Turn OFF  $V_{G2}$ .
5. Turn OFF  $V_{G1}$ .

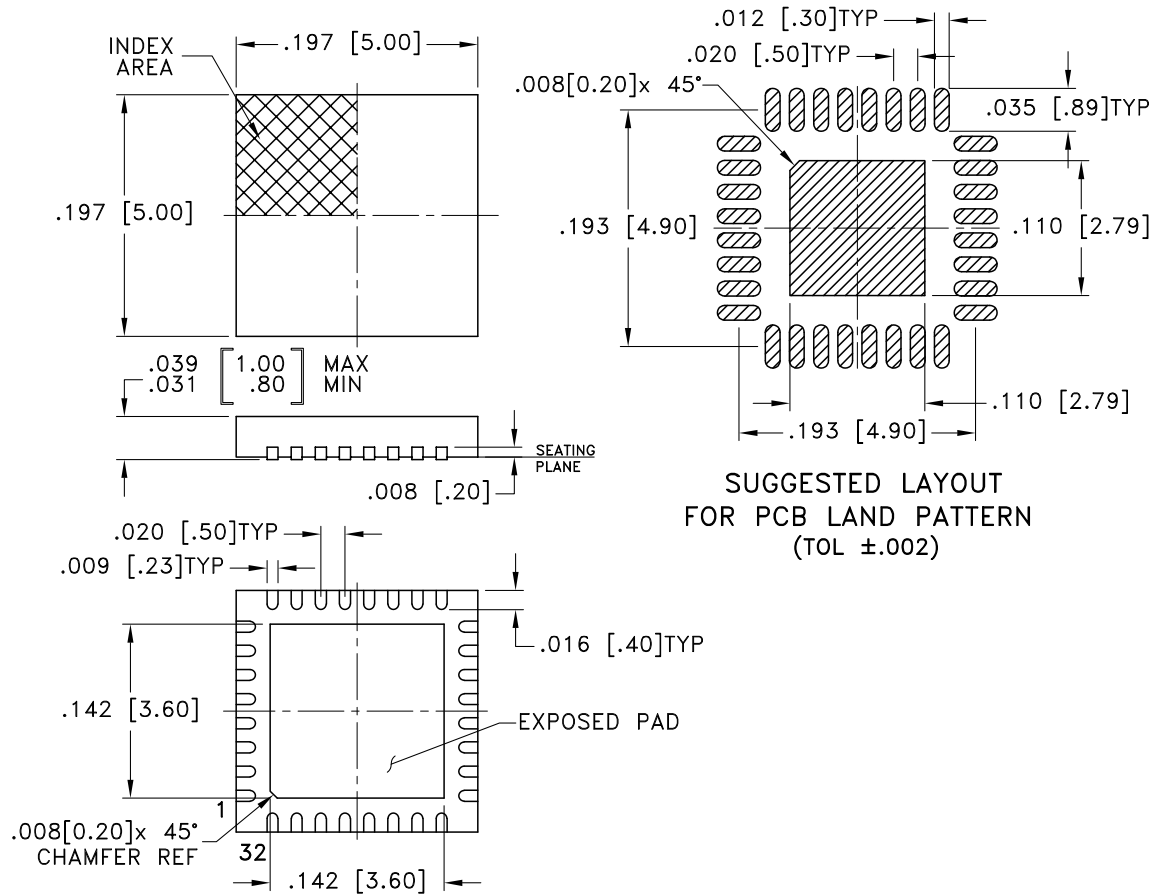
Figure 3. PMA5-63-2W+ Evaluation Board

Component	Value	Size	Part Number	Manufacturer
R1	301Ω	0402	RK73H1ETTP3010F	KOA SPEER ELECTRONICS
C1, C2, C3, C4, C5	4.7 μF	1206	12063C475KAT2A	AVX CORPORATION
C6, C7, C8	0.1 μF	0402	GRM155R71E104KE14D	MURATA
C9, C10, C11	100 pF	0402	GRM1555C1H101JA01D	MURATA
C12, C13, C14, C15	1 nF	0402	GRM1555C1H102JA01D	MURATA
L1, L2	36 nH	0402	0402AF-360XJLW	COILCRAFT
L3	1.1 μH	1008	1008AF-112XKRC	COILCRAFT



### CASE STYLE DRAWING

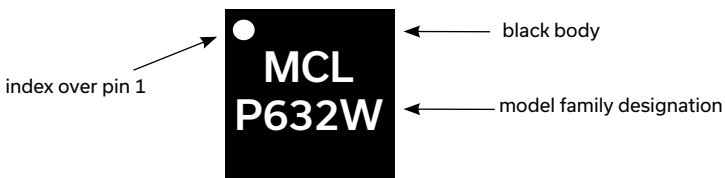
### PCB Land Pattern



Weight: .05 grams

Dimensions are in inches [mm]. Tolerances: 2 PI.±.01; 3PI.±.005 Inch

### PRODUCT MARKING



Marking may contain other features or characters for internal lot control



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50Ω 10 to 6000 MHz 2 W P<sub>SAT</sub>

ADDITIONAL DETAILED INFORMATION IS AVAILABLE ON OUR DASHBOARD [CLICK HERE](#)

<b>Performance Data &amp; Graphs</b>	Data Graphs S-Parameter (S2P Files) Data Set (.zip file)
<b>Case Style</b>	DG1677-10. Plastic package, exposed paddle, Lead Finish: Matte-Tin
<b>RoHS Status</b>	Compliant
<b>Tape &amp; Reel</b> Standard quantities available on reel	F68-1 7" reels with 10, 50, 100, 200, 500, 1K, or 2K devices
<b>Suggested Layout for PCB Design</b>	PL-789
<b>Evaluation Board</b>	TB-PMA5-63-2WC+ Gerber File
<b>Environmental Ratings</b>	ENV08T1

### NOTES

- A. Performance and quality attributes and conditions not expressly stated in this specification document are intended to be excluded and do not form a part of this specification document.
- B. Electrical specifications and performance data contained in this specification document are based on Mini-Circuit's applicable established test performance criteria and measurement instructions.
- C. The parts covered by this specification document are subject to Mini-Circuits standard limited warranty and terms and conditions (collectively, "Standard Terms"); Purchasers of this part are entitled to the rights and benefits contained therein. For a full statement of the standard terms and the exclusive rights and remedies thereunder, please visit Mini-Circuits' website at [www.minicircuits.com/terms/viewterm.html](http://www.minicircuits.com/terms/viewterm.html)

